| Part Number Customer |           |                                 |                                     |   |  |  |
|----------------------|-----------|---------------------------------|-------------------------------------|---|--|--|
| Category             | Parameter |                                 | Specification                       | Measurement Method                                  |  |  |
| OverallWafer         | 1.0       | Diameter                        | 150.00 +/- 0.30 mm                  |   |  |  |
|                      | 2.0       | Primary Flat Orientation        | <110> +/- 1 degree                  | Wafer Vendor  |  |  |
|                      | 3.0       | Primary Flat Length             | 57.50 +/- 2.50 mm                   | Wafer Vendor  |  |  |
|                      | 4.0       | Secondary Flat Orientation      | semi std/none                       |   |  |  |
|                      | 5.0       | Overall Thickness               | 752.00 +/- 28.00 μm                 | ADE 100%  |  |  |
|                      | 6.0       | Total Thickness Variation (TTV) | <5.00µm                             | Guaranteed by Process                               |  |  |
|                      | 7.0       | Bow                             | <60.00µm                            | ADE to ASTM F534, 20%<br>Best effort not guaranteed |  |  |
|                      | 8.0       | Warp                            | <60.00µm                            | ADE to ASTM F657, 20%<br>Best effort not guaranteed |  |  |
|                      | 9.0       | Edge Chips                      | 0                                   | Bright Light, 100% (note 2)                         |  |  |
|                      | 10.0      | Edge Exclusion                  | 5mm                                 |   |  |  |
| HandleSilicon        | 11.0      | Handle Growth Method            | CZ                                  | Wafer Vendor  |  |  |
|                      | 12.0      | Handle Orientation              | {100} +/- 1 degree                  | Wafer Vendor  |  |  |
|                      | 13.0      | Handle Thickness                | 550.00 +/- 25.00 μm                 | ADE, 100%   |  |  |
|                      | 14.0      | Handle Doping Type              | Р                                   | Wafer Vendor  |  |  |
|                      | 15.0      | Handle Dopant                   | Boron                               | Wafer Vendor  |  |  |
|                      | 16.0      | Handle Resistivity              | >0.01 Ohmcm                         | Wafer Vendor  |  |  |
|                      | 17.0      | Backside Finish                 | Polished with laser mark and oxide. | Guaranteed by process                               |  |  |
| BuriedOxide          | 18.0      | Oxide Type                      | Thermal                             |   |  |  |
|                      | 19.0      | Oxide Thickness                 | 20,000.00 +/- 2,000.00 A            | Nanospec centre point, 4%                           |  |  |
| DeviceSilicon        | 20.0      | Device Growth Method            | CZ                                  | Wafer Vendor  |  |  |
|                      | 21.0      | Device Orientation              | {100} +/- 1 degree                  | Wafer Vendor  |  |  |
|                      | 22.0      | Nominal Thickness               | 200.00 +/- 2.00 μm                  | ADE single point, 100%                              |  |  |
|                      | 23.0      | Device Doping Type              | Р                                   | Wafer Vendor  |  |  |
|                      | 24.0      | Device Dopant                   | Boron                               | Wafer Vendor  |  |  |
|                      | 25.0      | Device Resistivity              | >0.01 Ohmcm                         | Wafer Vendor  |  |  |
|                      | 26.0      | Voids                           | 0                                   | Bright Light, 100% (note 2)                         |  |  |
|                      | 27.0      | Scratches                       | 0                                   | Bright Light, 100% (note 2)                         |  |  |
|                      | 28.0      | Haze                            | none                                | Bright Light, 100% (note 2)                         |  |  |

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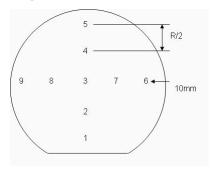
**Product Specification** 

1000.562301

| Part Number       |  | Customer  |                    |  |
|-------------------|--|---|--------------------|--|
| Category          | Parameter  | Specification   | Measurement Method |  |
| Shipping Details  | Wafer per box :  | Max 25  |                    |  |
|                   | Packaging :  | Taped Polypropylene Wafer Box<br>Empak, Ultrapak, 150.00mm<br>Antistatic Double Bagging |                    |  |
|                   | Lot Shipment Data  | Device Thickness<br>Bow / Warp Data<br>Handle and SOI Thickness                         |                    |  |
| Explanatory Notes | 1. Microscope inspection performed using microscope scan as below. 5x objective. |   |                    |  |

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information